

## **IN THE SPECIFICATION**

**Please add the following paragraph on page 1 after the title:**

### **CROSS REFERENCE TO RELATED APPLICATIONS**

This is a divisional of co-pending U.S. Application No. 09/580,961, filed on May 30, 2000, which claims priority to Japanese Application No. P11-148055, filed on May 27, 1999, which are incorporated herein by reference to the extent permitted by law.

**Amend page 1, third paragraph, as follows:**

A structure and fabrication method of a conventional AlGaInP-base visible light semiconductor laser device will be explained hereinafter referring to Fig. 5 6. Fig. 5 6 shows a cross-sectional view of the substrate showing a structure of an AlGaInP-base semiconductor laser device.

**Amend page 1, fourth paragraph, as follows:**

An AlGaInP-base semiconductor laser device 10 has on a GaAs substrate 12 a stacked structure comprises a lower cladding layer 14 made of n-AlGaInP, an active layer 16, an upper cladding layer 18 made of p-AlGaInP, and a contact layer 20 made of p-GaAs, and all layers are epitaxially grown in this order.

**Amend page 2, sixth paragraph, as follows:**

In the process of etching the stack-structured portion to form the mesa-structured portion after the epitaxial growth, etching with an acid of such epitaxially grown layer having the growth defect will result in formation of a pit-like shape defect portion 28 of several to tens  $\mu\text{m}$  diameter reaching the GaAs substrate 12 as shown in Fig. 6 7, since the portion of the growth defect is labile to acid and shows a high etchrate etch rate.

**Amend page 9, third paragraph, as follows:**

Fig. 4d 5 is a sectional view showing, as continued from Fig. 4c, layer structures corresponded to a process step for fabricating a semiconductor layer device according to Example 4;

**Amend page 9, fourth paragraph, as follows:**

Fig. 5 6 is a sectional view of a substrate showing a conventional visible light semiconductor laser device; and

**Amend page 9, fifth paragraph, as follows:**

Fig. 6 7 is a sectional view of a substrate for explaining the pit-like recess.

**Amend page 14, sixth paragraph, as follows:**

In a semiconductor laser device 66 of Example 4, as shown in Fig 4d 5, a an outermost surface of a wall plane of a pit-like recess 40, occurred so as to penetrate the n-GaAs layer 22 (current blocking layer), upper cladding layer 18, active layer 16 and lower layer 14, and to reach the GaAs substrate 12, is converted into a layer 62 with a higher resistivity by ion implantation of boron.

**Amend page 15, first paragraph, as follows:**

Next, a method for fabricating the semiconductor laser device 66 according to Example 4 will be explained referring to Figs. 4a to 4d 5.